

Photosensitive inverters and light-to-frequency conversion circuits based on transition metal dichalcogenides field effect transistors

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Recently transition metal dichalcogenides (TMDCs) such as MoS_2 , WSe_2 , MoTe_2 , WS_2 and others have been emerged and actively researched as one of next generation semiconductors for extending Moore's law. Among a variety of novel properties for TMDCs, one of interesting properties is to modulate energy bandgap (E_g) in variation of number of layers. In this study, for the improvement of noise immunity for IoT sensor systems, photo sensitive inverters and their light-to-frequency conversion circuits (LFCs) are proposed and experimentally demonstrated by using the platform comprised of an enhancement MoS_2 driver with light-shield layers (LSLs) (or GaN FET drivers) and MoS_2 depletion load. Moreover, for energy efficient circuits, complementary photo- sensitive inverters based on p-type MoTe_2 and n-type MoS_2 FETs are demonstrated. For the better understanding on performance of LFCs, we systematically studied basic design rules on LFCs via

experimentally measured voltage transfer characteristics of photo-sensitive inverters and their spice simulation with their extracted model parameters based on RPI model (i.e., SILVACO, Smart-spice; level 36). The simulation results illustrate that key parameters of ring oscillators (ROs) such as oscillation frequency (f_{osc}) and peak-to peak voltage (V_{p-p}) can be systematically controlled by inverter parameters such as noise margin, voltage gains associated with electrical parameters (i.e., V_{th} , SS, current on/off ratio, field effect mobility, etc). In the present study, experimental implementation of photosensitive inverters based on MoS_2 , MoTe_2 , and GaN FETs, etc. and their systematic validation on performance via spice simulation yield insightful design rules required for reliable operation of LFCs, potentially contributing to emerging IoT security systems.

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